



# PerF≝T<sup>™</sup>Power Transistor

#### **FEATURES**

- Ultra-low On-resistance
- 100% UIS and Rg tested
- RoHS Compliant
- Halogen-Free according to IEC 61249-2-21

#### **APPLICATIONS**

- DC-DC Converters
- · Solenoid and Motor Drivers
- Load Switch

PRODUCT SUMMARY				
PARAMETER		VALUE	UNIT	
$V_{ t DS}$		40	V	
	$V_{GS} = 10V$	7	)	
R <sub>DS(on)</sub> (max)	$V_{GS} = 7V$	8.4	mΩ	
$Q_g$	V <sub>GS</sub> = 10V	21	nC	











Pin 5 , 6 , 7 , 8 Drain

Pin 4
Gate

Source
Pin 1 , 2 , 3

Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current, Silicon limited	$T_C = 25^{\circ}C$	$I_{D}$	56	Α
	$T_C = 25^{\circ}C$	I <sub>D</sub>	54	
Continuous Drain Current (Note 1)	$T_C = 100$ °C		35	А
	$T_A = 25$ °C		14	
Pulsed Drain Current		I <sub>DM</sub>	216	Α
Single Pulse Avalanche Current (Note 2)		I <sub>AS</sub>	17.3	А
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	44.7	mJ
Total Dawer Dissipation	T <sub>C</sub> = 25°C	D	36	W
Total Power Dissipation	T <sub>C</sub> = 125°C	$P_{D}$	7.1	VV
Operating Junction and Storage Temperature Range		$T_J,T_STG$	-55 to +150	°C

THERMAL RESISTANCE				
PARAMETER	SYMBOL	MAXIMUM	UNIT	
Thermal Resistance – Junction to Case	R <sub>eJC</sub>	3.5	°C/W	
Thermal Resistance – Junction to Ambient	$R_{\Theta JA}$	53	°C/W	

**Note**:  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JC}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.

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ELECTRICAL CHARACTERISTICS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 1mA$	BV <sub>DSS</sub>	40			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2.4	3	3.6	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
	$V_{GS} = 0V, V_{DS} = 40V$				1	
Drain-Source Leakage Current				100	μΑ	
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 27A$	- R <sub>DS(on)</sub> -		6.2	7	mΩ
(Note 3)	$V_{GS} = 7V, I_D = 27A$			7.2	8.4	
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 7A$	g <sub>fs</sub>		36		S
Dynamic						
Total Gate Charge	$V_{GS} = 7V, V_{DS} = 20V,$ $I_{D} = 14A$	$Q_g$		15		
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 20V,$ $I_{D} = 14A$	$Q_g$		21		nC
Gate-Source Charge		$Q_{gs}$		5.6		
Gate-Drain Charge		$Q_{gd}$		4.8		
Input Capacitance		C <sub>iss</sub>		1233		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 25V,$	C <sub>oss</sub>		249		pF
Reverse Transfer Capacitance	f = 1.0MHz	$C_{rss}$		31		
Gate Resistance	f = 1.0MHz	$R_{g}$		1.6		Ω
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 20V,$ $I_{D} = 14A, R_{G} = 1.6\Omega$	$t_{d(on)}$		10		
Rise Time		t <sub>r</sub>		45		
Turn-Off Delay Time		$t_{d(off)}$		19		nS
Fall Time		t <sub>f</sub>		6.1		
Source-Drain Diode						
Diode Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 27A$	V <sub>SD</sub>			1.1	V
Reverse Recovery Time	I <sub>S</sub> = 14A,	t <sub>rr</sub>		28		nS
Reverse Recovery Charge	di/dt = 100A/µs	$Q_{rr}$		20		nC

### Notes:

- 1. Package current limit.
- 2. L = 0.3mH,  $V_{GS} = 10V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$ .
- 3. Pulse test: Pulse Width  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 4. Switching time is essentially independent of operating temperature.

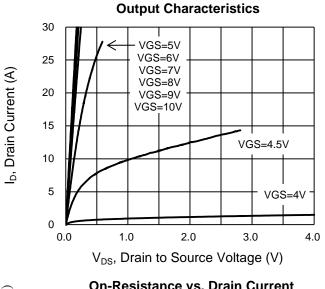
# **ORDERING INFORMATION**

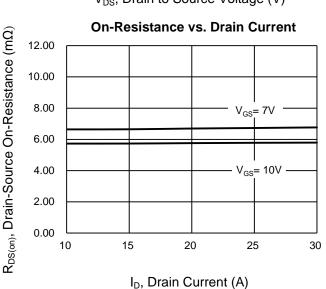
ORDERING CODE	PACKAGE	PACKING
TSM070NH04CV RGG	PDFN33	5,000pcs / 13" Reel

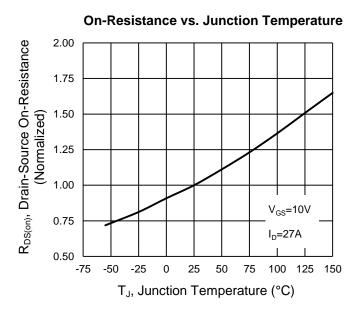


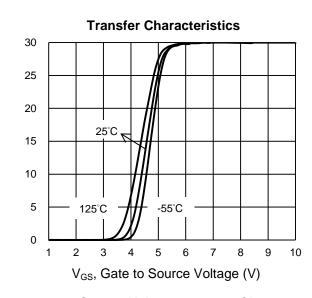
# **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)





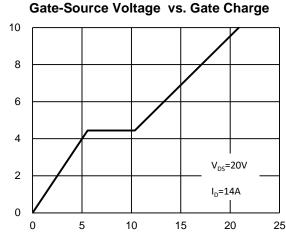


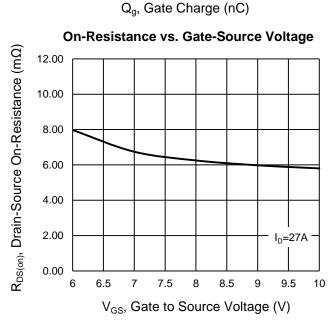


Ip, Drain Current (A)

V<sub>GS</sub>, Gate to Source Voltage (V)

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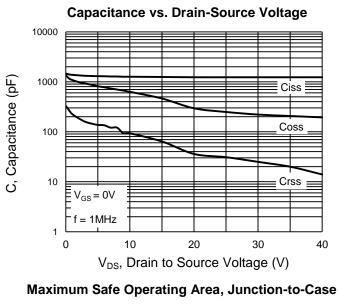


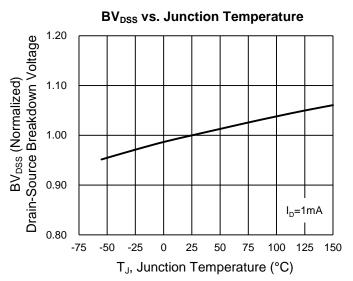


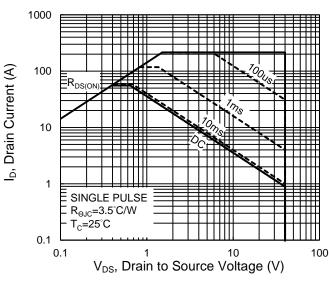


#### **CHARACTERISTICS CURVES**

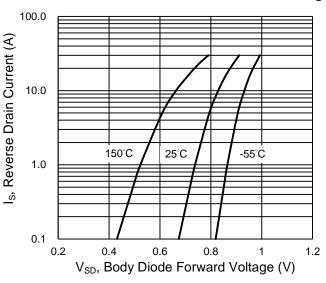
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



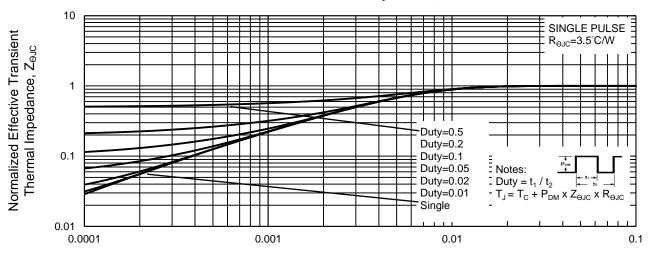




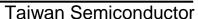
#### Source-Drain Diode Forward Current vs. Voltage



#### Normalized Thermal Transient Impedance, Junction-to-Case



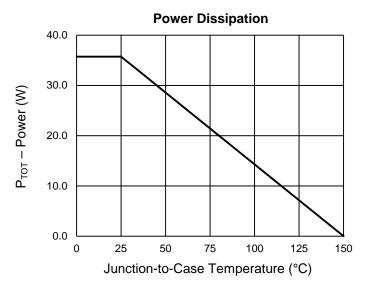
t, Square Wave Pulse Duration (sec)

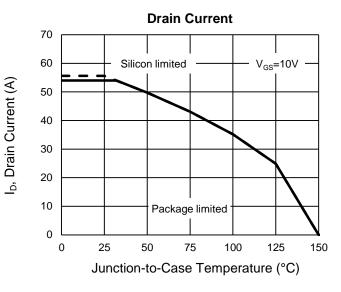




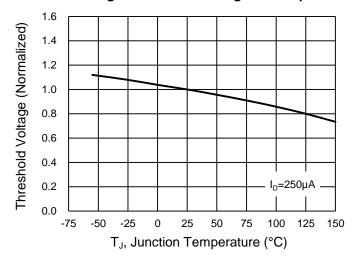
### **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)





### Normalized gate threshold voltage vs Temperature



Version: A2207

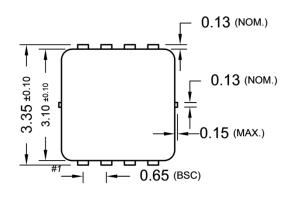
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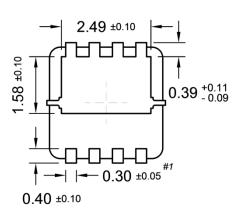


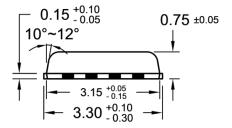
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# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

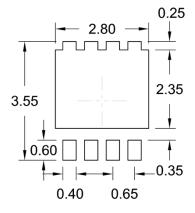
#### PDFN33







# SUGGESTED PAD LAYOUT (Unit: Millimeters)



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#### **MARKING DIAGRAM**



Y = Year Code

**WW** = Week Code (01~52)

 $\mathbf{L}$  = Lot Code (1~9,A~Z)

**F** = Factory Code



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